

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9	(US-20030075730-\$).did. or (US-4881105-\$ or US-4947226-\$ or US-5177576-\$ or US-5561308-\$ or US-5937296-\$ or US-6127712-\$ or US-6362025-\$).did. or (JP-58003287-\$).did.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/27 08:53
L2	7	1 and gate.ab.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:02
L3	6	("4521795"   "5142640"   "5160491"   "5242845"   "5578508"   "5627393"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/27 08:03
L4	19	("4521795").URPN.	USPAT	OR	ON	2005/12/27 08:09
L5	32	("4881105").URPN.	USPAT	OR	ON	2005/12/27 08:10
L6	812	257/410.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:30
L7	411	257/332.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:38
L8	544	257/331.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:48
L9	762	257/329.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:48
L10	1	((first adj semiconductor) and (second adj semiconductor) and (third adj semiconductor) and trench and (hollow adj portion) and (bottom with trench)).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/27 08:55
S1	43	(vertical with transistor) and (gate with hollow)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:22

S2	13	S1 and (gate with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:04
S3	511	(vertical with (gate or transistor)) and (gate with hollow)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:23
S4	393	S3 and gate.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:23
S5	22	S4 and (gate with trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:40
S6	505	(trench adj gate) and (dielectric with (side or sidewall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:40
S7	1	S6 and (gate with (air or (air adj gap)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:42
S8	4	S6 and (gate with hollow)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:44
S9	20	transistor and (hollow adj gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:48
S10	12071	transistor and (trench with gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:48
S11	7768	S10 and (gate with (side or sidewall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:49

S12	148	S11 and hollow	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:49
S13	80	S12 and gate.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 11:49
S14	7	("4728621"   "5604218"   "5736446"   "5770507"   "6087208"   "6127232"   "6130121").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/22 11:56
S15	9	(US-20030075730-\$).did. or (US-4881105-\$ or US-4947226-\$ or US-5177576-\$ or US-6362025-\$ or US-6127712-\$ or US-5561308-\$ or US-5937296-\$).did. or (JP-58003287-\$).did.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/22 12:01
S16	1231	257/330.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/27 08:22